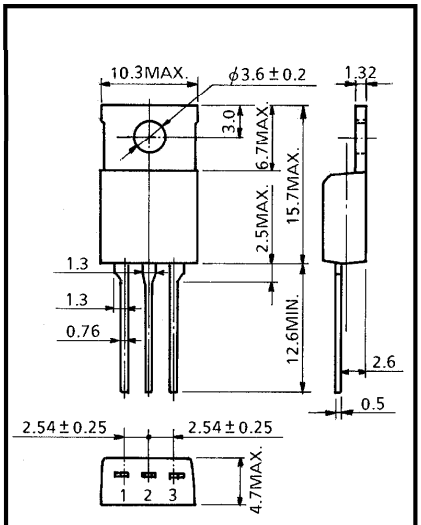
TOSHIBA THYRISTOR SILICON PLANAR TYPE

SF10G41A, SF10J41A

MEDIUM POWER CONTROL APPLICATIONS

Unit in mm

- Repetitive Peak Off-State Voltage : V_{DRM} } =400, 600V
  Repetitive Peak Reverse Voltage : V_{RRM} }
- Average On-State Current : $I_{T(AV)}$ =10A
- Gate Trigger Current : I_{GT}=15mA (Max.)



1. CATHODE
2. ANODE (HEAT SINK)
3. GATE

JEDEC	TO-220AB
EIAJ	SC-46
TOSHIBA	13-10G1B

Weight : 2g

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	SF10G41A	V_{DRM} V_{RRM}	400	V
	SF10J41A		600	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive<5ms, T_j=0~125°C)	SF10G41A	V_{RSM}	500	V
	SF10J41A		720	
Average On-State Current (Half Sine Waveform Tc=79°C)		$I_{T(AV)}$	10	A
R.M.S On-State Current		$I_{T(RMS)}$	16	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	160 (50Hz)	A
			176 (60Hz)	
I^2t Limit Value		I^2t	125	A^2s
Critical Rate of Rise of On-State Curret		di / dt	100	A / μs
Peak Gate Power Dissipation		P_{GM}	5	W
Average Gate Power Dissipation		$P_{G(AV)}$	0.5	W
Peak Forward Gate Voltage		V_{FGM}	10	V
Peak Reverse Gate Voltage		V_{RGM}	−5	V
Peak Forward Gate Current		I_{GM}	2	A
Junction Temperature		T_j	−40~125	°C
Storage Temperature Range		T_{stg}	−40~125	°C

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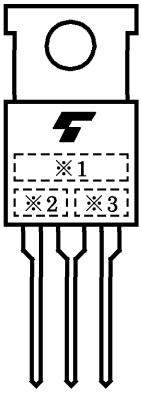
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

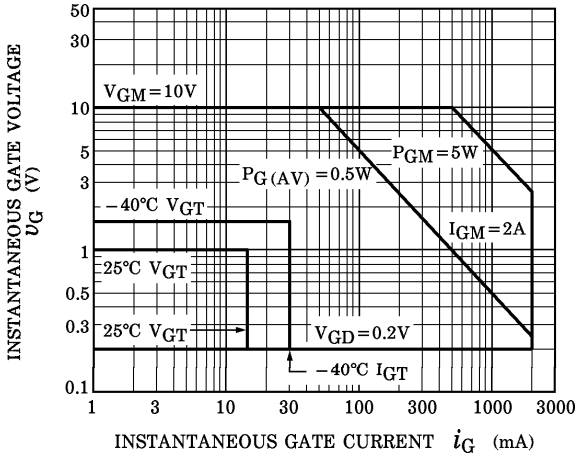
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	I_{DRM} I_{RRM}	$V_{DRM}=V_{RRM}=$Rated	—	10	μA
Peak On-State Voltage	V_{TM}	$I_{TM}=30A$	—	1.6	V
Gate Trigger Voltage	V_{GT}	$V_D=6V$, $R_L=10\Omega$	—	1.0	V
Gate Trigger Current	I_{GT}		—	15	mA
Gate Non-Trigger Voltage	V_{GD}	$V_D=$Rated$\times 2/3$, Tc=125°C	0.2	—	V
Critical Rate of Rise of Off-State Voltage	dv / dt	$V_{DRM}=$Rated$\times 2/3$, Tc=125°C Exponential Rise	100	—	V / μs
Holding Current	I_H	$V_D=6V$, $I_{TM}=1A$	—	40	mA
Latching Current	I_L	$V_D=6V$, f=50Hz, $t_{gw}=50\mu S$ $i_G=30mA$	—	60	mA
Thermal Resistance	$R_{th\ (j-c)}$	Junction to Case	—	2.0	°C / W

MARKING

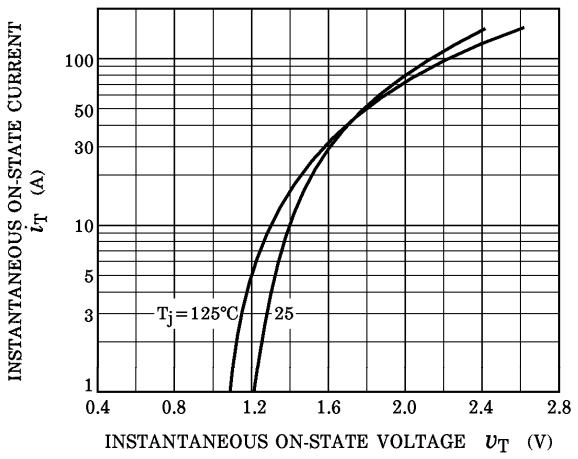


NUMBER	SYMBOL		MARK
※1	TYPE	SF10G41A	SF10G41
		SF10J41A	SF10J41
※2		SF10G41A, SF10J41A	A
※3	Lot Number □□ Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year)		Example 8A : January 1998 8B : February 1998 8L : December 1998

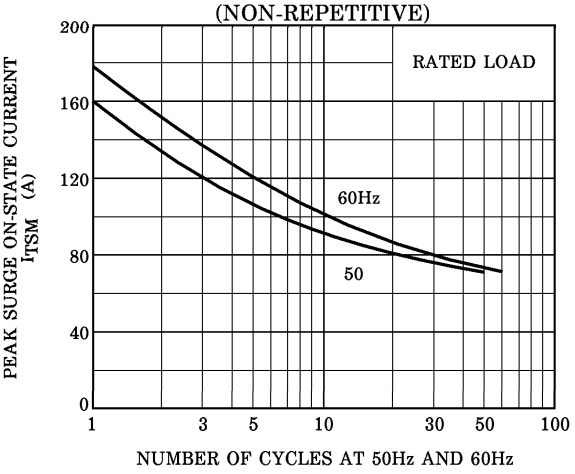
GATE TRIGGER CHARACTERISTIC



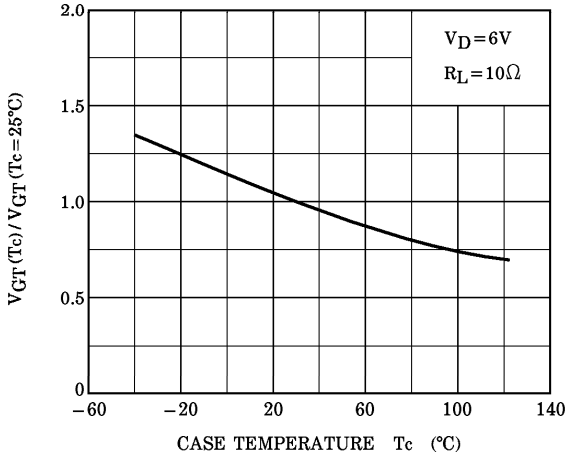
i_T – v_T



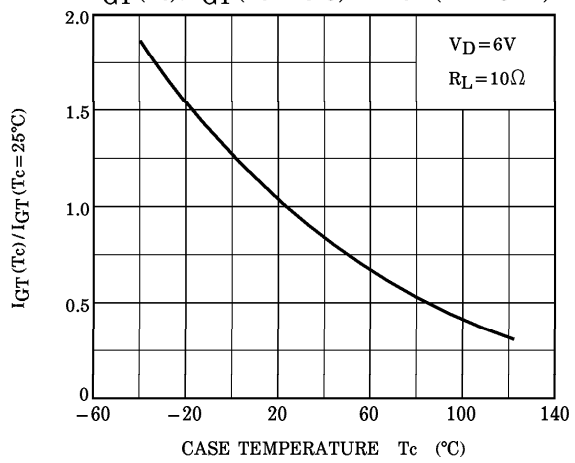
SURGE ON-STATE CURRENT
(NON-REPETITIVE)



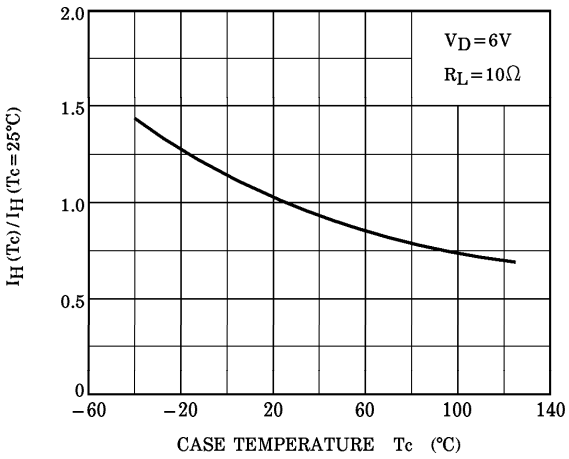
V_{GT} (Tc) / V_{GT} (Tc=25°C) – Tc (TYPICAL)



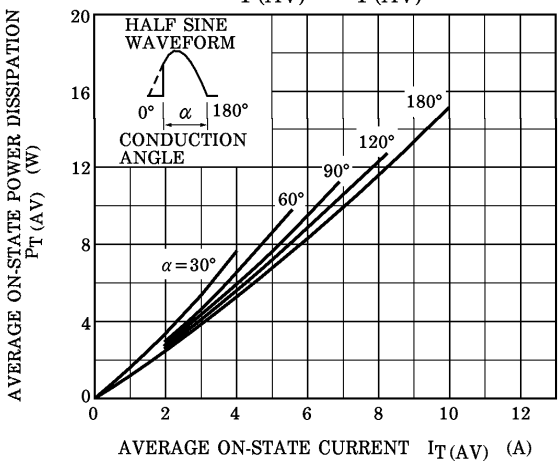
I_{GT} (Tc) / I_{GT} (Tc=25°C) – Tc (TYPICAL)



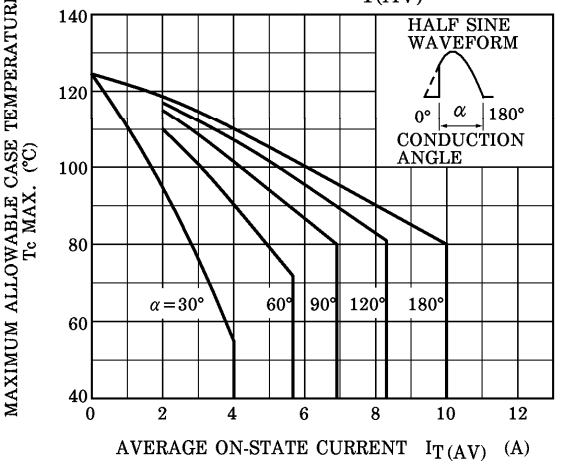
I_H (Tc) / I_H (Tc=25°C) – Tc (TYPICAL)



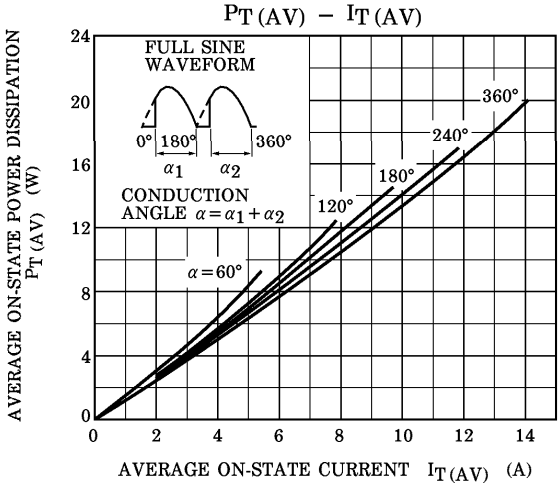
$P_{T(AV)}$ – $I_{T(AV)}$



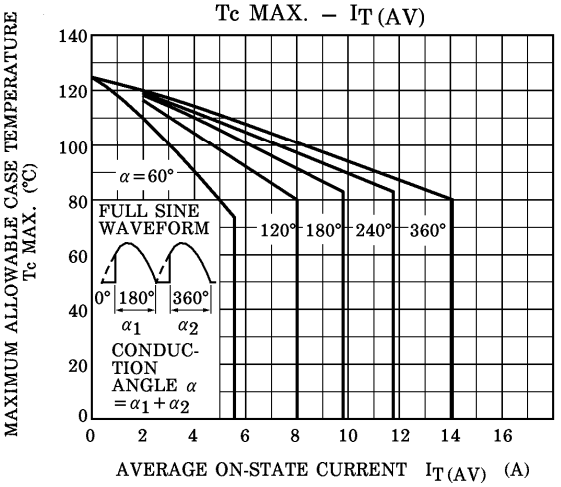
T_c MAX. – $I_{T(AV)}$



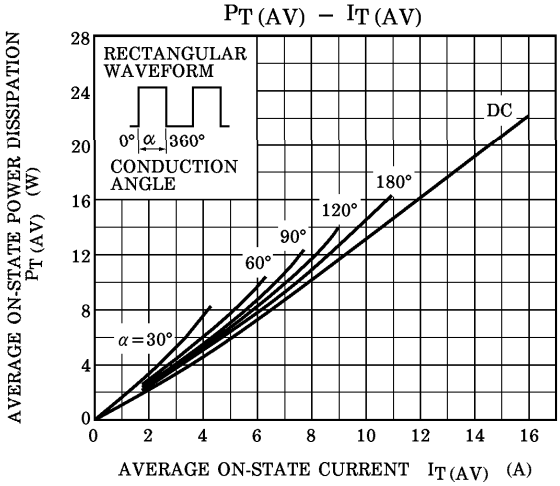
$P_{T(AV)}$ – $I_{T(AV)}$



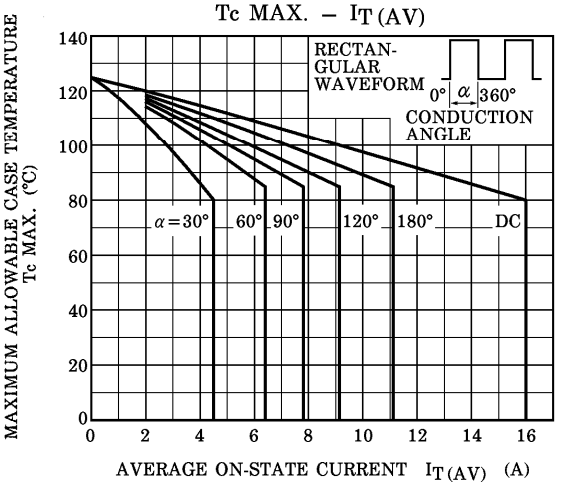
T_c MAX. – $I_{T(AV)}$



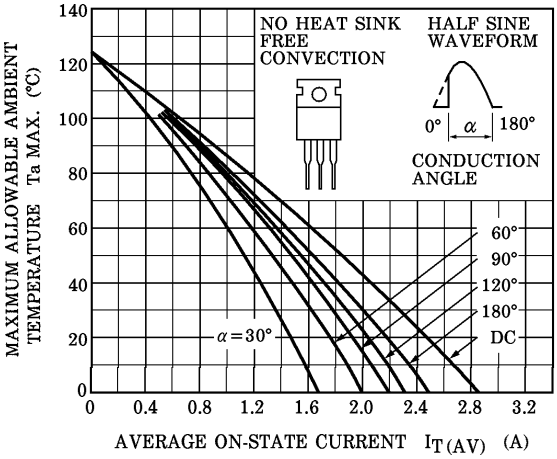
$P_{T(AV)}$ – $I_{T(AV)}$



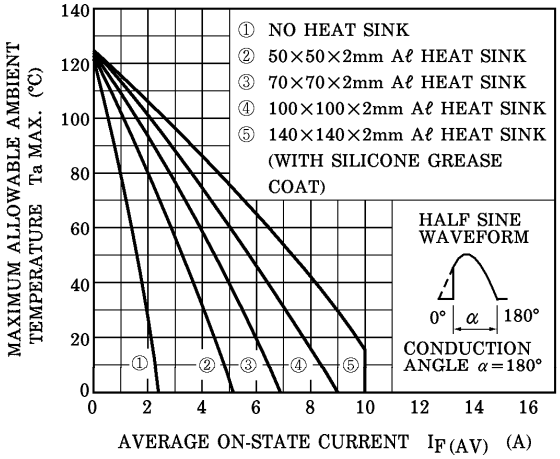
T_c MAX. – $I_{T(AV)}$



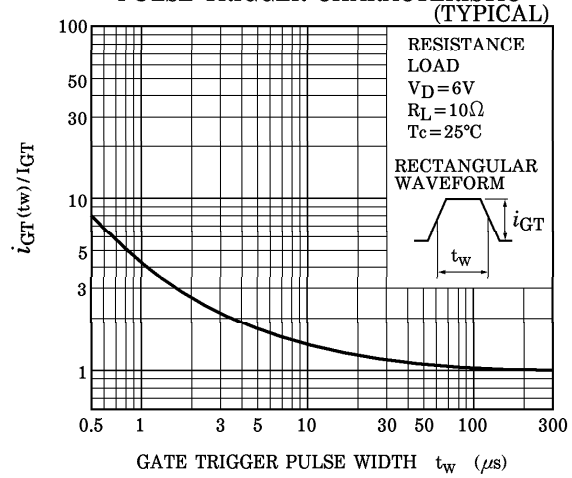
Ta MAX. – $I_{T(AV)}$



Ta MAX. – $I_{T(AV)}$



PULSE TRIGGER CHARACTERISTIC (TYPICAL)



TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)